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Application No. : ~~10/687,203~~

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First Named Inventor: M. YOSHIDA

Group Art Unit :

Examiner Name :

Attorney Docket No. : FUSA 20.686

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	U.S. Patent Document	Kind Code if known ²	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns Lines Where Relevant Passages or Relevant Figures Appear
LP		5,225,702		CHATTERJEE	07/06/1993	
		5,465,189		POLGREEN, et al.	11/07/1995	
		5,502,317		DUVVURY	03/26/1996	
		2003/0075726		KER, et al.	04/24/2003	
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✓		2002/0130366		MORISHITA	09/19/2002	

FOREIGN DOCUMENTS

Examiner Initials	Cite No. ¹	Foreign Patent Document Office ³ Number ⁴ Kind Code ⁵ (if known)	Country	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY/Y	Pages, Columns Lines Where Relevant Passages or Relevant Figures Appear
LP		09-107074	JP	TEXAS INSTR INC <TI>	04/22/1997	
		2003-203985	JP	NEC ELECTRONICS CORP	07/18/2003	

Other Prior Art-Non Patent Literature Documents

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), data, page(s), volume-issue number(s), publisher, country, where published, source.	Applicant check here if English language translation attached
LP		AMERASEKERA, et al., "SUBSTRATE TRIGGERING AND SALICIDE EFFECTS ON ESD PERFORMANCE AND PROTECTION CIRCUIT DESIGN IN DEEP SUBMICRON CMOS PROCESSES" 1995 IEEE, pp. 547-549, 0-7803-2700-4	
		MERGENS, et al., "HIGH HOLDING CURRENT SCRS (HHI-SCR) FOR ESD PROTECTION AND LATCH-UP IMMUNE IC OPERATION" 2002 EOS/ESD SYMPOSIUM, pp. 1-8	
		CHATTERJEE, et al., "A LOW-VOLTAGE TRIGGERING SCR FOR ON-CHIP ESD PROTECTION AT OUTPUT AND INPUT PADS" IEEE ELECTRON DEVICE LETTERS, VOL. 12, NO. 1, JANUARY 1991 IEEE pp. 21-22	
Examiner Signature		Long PHAM	Date Considered 11/19/07

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP (409). Draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1⁶ if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

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